Single Output LNB Supply and Control Voltage Regulator

General Description

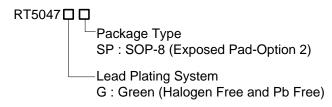
The RT5047 is a highly integrated voltage regulator and interface IC, specifically design for supplying power and control signals from advanced satellite set-top box (STB) modules to the LNB down-converter in the antenna dish or to the multi-switch box.

The device is consists of the independent current-mode boost controller and low dropout linear regulator along with the circuitry required for 22kHz tone shaping to support $DiSEqC^{TM}1.x$ communications.

The RT5047 has fault protection (over-current, over-temperature and under-voltage lockout).

The RT5047 are available in a SOP-8 (Exposed Pad) package to achieve optimized solution for thermal dissipation.

Ordering Information



Note :

Richtek products are :

- ► RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- Suitable for use in SnPb or Pb-free soldering processes.

Features

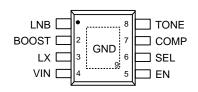
- Wide Input Supply Voltage Range : 8V to 16V
- Output Current Limit of 550mA with 45ms timer
- Low Noise LNB Output Voltage (13.3V and 18.3V by SEL Pin, 14.3V and 19.3V by COMP Pin)
- ±3% High Accuracy for 0mA to 500mA Current Output
- Push-Pull Output Stage minimizes 13.3V to 18.3V and 18.3V to 13.3V Output Transition Time
- External 22kHz Tone Input
- Meet DiSEqCTM1.x Protocol
- Output Short Circuit Protection
- Over-Temperature Protection

Applications

- LNB Power Supply and Control for Satellite Set-Top Box
- Analog and Digital Satellite Receivers/Satellite TV, Satellite PC cards

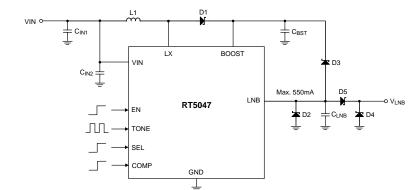
Pin Configuration

(TOP VIEW)



SOP-8 (Exposed Pad)

Simplified Application Circuit







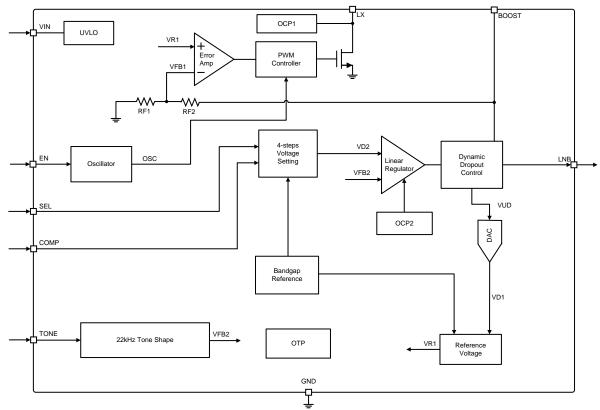
Marking Informaton

RT5047GSP : Product Number YMDNN : Date Code

Functional Pin Description

Pin No.	Pin Name	Pin Function	
1	LNB	Output voltage for LNB.	
2	BOOST	Boost output and tracking supply voltage to LNB.	
3	LX	Switching node of DC-DC boost converter.	
4	VIN	Power supply input.	
5	EN	LNB output enable.	
6	SEL	LNB output voltage selection pin (Low is for 13.3V, high is for 18.3V).	
7	COMP	LNB output voltage compensate pin.	
8	TONE	22kHz TONE input.	
9 (Exposed Pad)	GND	Ground. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.	

Functional Block Diagram



RT5047 GSPYMDNN

Operation

The RT5047 integrates a current mode boost converter and linear regulator. Use the SEL pin to control the LNB voltage and the boost converter track is at least greater 850mV than LNB voltage. The boost converter is the high efficiency PWM architecture with 700kHz operation frequency. The linear regulator has the capability to source current up to 550mA during continuous operation. All the loop compensation, current sensing, and slope compensation functions are provided internally.

OCP

Both the boost converter and the linear regulator have independent current limit. In the boost converter (OCP1), this is achieved through cycle-by-cycle internal current limit (typ. 3A). In the linear regulator (OCP2), when the linear regulator exceeds OCP more than 48ms, the LNB output will be disabled and re-start after 1.8s.

Tone Circuit

This circuit is used for tone generation. Use the TONE pin to control output amplitude of LNB.

ΟΤΡ

When the junction temperature reaches the critical temperature (typically 150°C), the boost converter and the linear regulator are immediately disabled.

UVLO

The UVLO circuit compares the VIN with the UVLO threshold (7.7V rising typically) to ensure that the input voltage is high enough for reliable operation. The 350mV (typ.) hysteresis prevents supply transients from causing a shutdown.

PWM Controller

The loop compensation, current sensing, and slope compensation functions are provided internally.

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Absolute Maximum Ratings (Note 1)

Supply Input Voltage, VIN	0.3V to 28V
Output Voltage LNB, LX and BOOST Pins	0.3V to 30V
Others Pin to GND	0.3V to 6V
• Power Dissipation, $P_D @ T_A = 25^{\circ}C$	
SOP-8 (Exposed pad)	3.44W
Package Thermal Resistance (Note 2)	
SOP-8 (Exposed pad), θ_{JA}	29°C/W
SOP-8 (Exposed pad), θ_{JC}	2°C/W
Lead Temperature (Soldering, 10 sec.)	260°C
Junction Temperature	150°C
Storage Temperature Range	–65°C to 150°C
ESD Susceptibility (Note 3)	
HBM (Human Body Model)	2kV

Recommended Operating Conditions (Note 4)

٠	Supply Input Voltage	8V to 16V
•	Ambient Temperature Range	–40°C to 85°C
•	Junction Temperature Range	–40°C to 125°C

Electrical Characteristics

$(V_{IN (typ.)} = 12V, V_{IN} = 8V \text{ to } 16V, T_A = 25^{\circ}C, \text{ unless otherwise spectrum}$	ified)
---	--------

Parameter Symbol Test Conditions		Min	Тур	Мах	Unit	
General						
NB Output Accuracy, Load and Line Regulation E_{RR} Relative to selected V _{LNB} target level, I _{LNB} = 0 to 450mA		-3		3	%	
	I _{IN_OFF}	EN = 0, LNB output disabled		0.3	0.5	mA
Supply Current	I _{IN_ON}	EN = 1, VLNB = 18.3V, Tone = 0V		10	18	mA
	I _{IN_ON}	EN = 1, VLNB = 18.3V, 22kHz TONE Input		16	28	mA
Boost Switch On Resistance	R _{DS(ON)}	I _{LNB} = 450mA		150	300	mΩ
Switching Frequency	fsw			700	800	kHz
Switch Current Limit I_{LIMSW} $V_{IN} = 10V, V_{LNB} = 20.5V$			3		А	
Linear Regulator Voltage V _{DROP} V _{BOOST} -V _{LNB} , I _{LNB} = 450mA			0.85		V	
Output Voltage Rise Time	ge Rise Time T_{R_LNB} For $V_{LNB} = 13.3V \rightarrow 18.3V$, $C_{LNB} = 100nF$, $I_{LNB} = 450mA$			3	10	ms
Output Voltage Pull-Down Time T_{F_LNB} For $V_{LNB} = 18.3V \rightarrow 13.3V$, $C_{LNB} = 100nF$, $I_{LNB} = 0mA$			3	10	ms	

RT5047

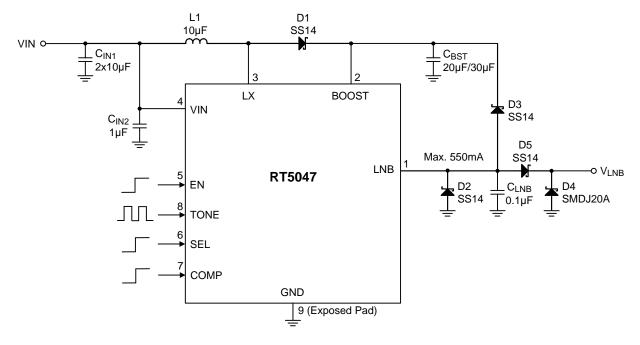
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Ripple and Noise on LNB Output	Vrip_pp	20MHz bandwidth limit (GBD)		20		mVpp	
Load Regulation	Vout_load	$V_{LNB} = 13.3V$, $I_{LNB} = 50mA$ to 450mA		38	76	6 mV	
Load Regulation		$V_{LNB} = 18.3V$, $I_{LNB} = 50mA$ to 450mA		45			
Line Regulation		$V_{IN} = 9$ to 14V, $V_{LNB} = 13.3V$, $I_{LNB} = 50$ mA	-10		10	- mV	
	VOUT_LINE	$V_{IN} = 9$ to 14V, $V_{LNB} = 18.3V$, $I_{LNB} = 50mA$	-10		10		
Protection	Γ			1	[
Output Over-Current Limit	I _{LIM_LNB1}	V _{LNB} = 13.3V/18.3V	500	550	650	mA	
Output Over-Current Disable Time	T _{DIS_ON}	V _{LNB} short to GND		45		ms	
Output Over-Current Disable Time	T _{DIS_OFF}	V _{LNB} short to GND (GBD)		1800		ms	
VIN Under-Voltage Lockout Threshold	Vuvlo	V _{IN} falling		7.35		V	
VIN Turn On Threshold	VIN_TH	V _{IN} rising		7.7	8	V	
VIN Under-Voltage Lockout Hysteresis	VUVLOHYS			350		mV	
OTP Threshold	T _{OTP}			140		°C	
OTP Hysteresis	TOTPHYS			15		°C	
TONE	I		1			1	
TONE Frequency	FTONE		20	22	24	kHz	
TONE Amplitude, Peak to Peak	VTONE_PP	I _{LNB} = 50 to 450mA, C _{LNB} = 200nF	550	700	900	mV _{PP}	
TONE Duty Cycle	DC _{TONE}	$I_{LNB} = 0$ to 450mA, $C_{LNB} = 570$ nF	40	50	60	%	
TONE Rise Time	T _{RTONE}	$I_{LNB} = 0$ to 450mA, $C_{LNB} = 570$ nF	5	10	15	μs	
TONE Fall Time	T _{FTONE}	$I_{LNB} = 0$ to 450mA, $C_{LNB} = 570$ nF	5	10	15	μS	
	V _{TONE} _H		1.2			V	
TONE Logic Input	V _{TONE_L}				0.4	V	
TONE Input Leakage	Itonelkg			5	10	μA	
ENABLE, SEL Pins							
	Ven_h		1.2			V	
EN Logic Input	Ven_L				0.4	V	
EN Input Leakage	IENLKG			5	10	μA	
	V _{SEL_H}		1.2			V	
SEL Logic Input	V _{SEL_L}				0.4	V	
SEL Input Leakage	ISELLKG			5	10	μA	

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- Note 1. Stresses beyond those listed "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions may affect device reliability.
- Note 2. θ_{JA} is measured at $T_A = 25^{\circ}C$ on a high effective thermal conductivity four-layer test board per JEDEC 51-7. θ_{JC} is measured at the exposed pad of the package.
- Note 3. Devices are ESD sensitive. Handling precaution is recommended.
- Note 4. The device is not guaranteed to function outside its operating conditions.
- Note 5. Operation at V_{IN} = 16V may be limited by power loss in the linear regulator.

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Typical Application Circuit

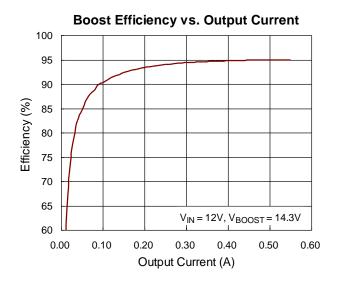


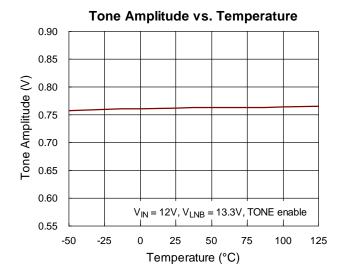
Note :

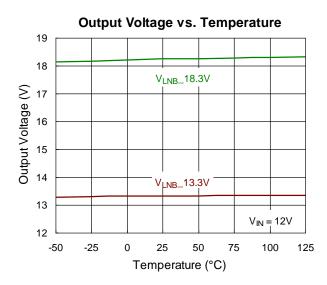
- 1. D2, D3, D4, D5 are used for surge protection.
- 2. The capacitor C3 should not be less than 1μ F for the power stability.
- 3. EN, TONE and SEL are connected to microcontroller directly.

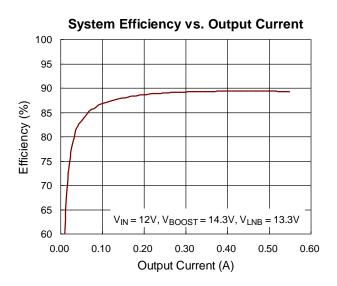


Typical Operating Characteristics

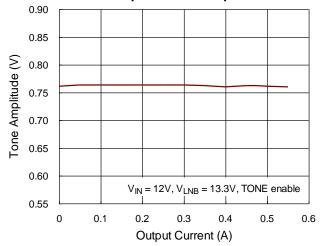


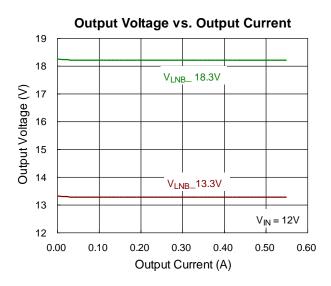






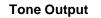
Tone Amplitude vs. Output Current

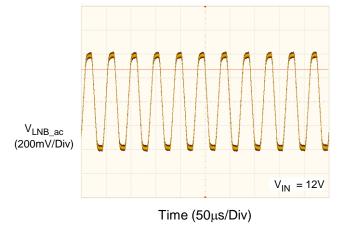


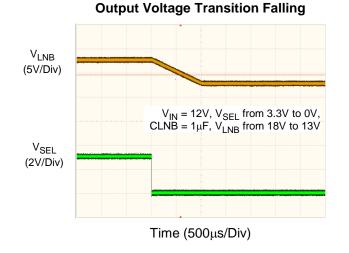


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Over Current Protect vs. Temperature 0.70 0.65 Current (A) 0.60 0.55 V_{IN} = 12V, V_{LNB} = 13.3V 0.50 -25 0 25 50 75 100 125 Temperature (°C)

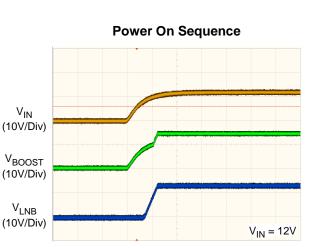






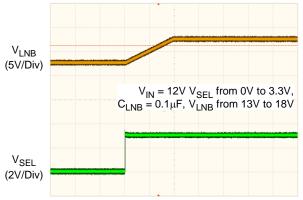
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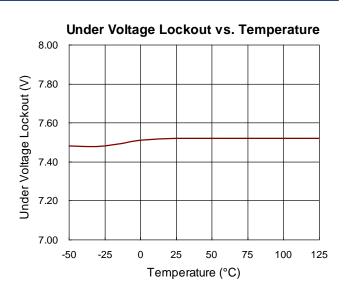


Time (5ms/Div)

Output Voltage Transition Rising



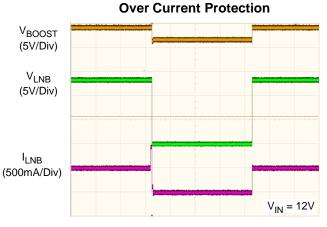
Time (500µs/Div)



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Time (500ms/Div)

Application Information

Boost Converter/Linear Regulator

The 5047 integrates a current-mode boost converter and linear regulator. Use the SEL pin to control the LNB voltage and the boost converter track is at least greater 800mV than the LNB voltage. The boost converter is high efficiency PWM architecture with 700kHz operation frequency. The linear regulator has the capability to source current up to 550mA during continuous operation. All the loop compensation, current sensing, and slope compensation functions are provided internally.

The RT5047 has current limiting on the boost converter and the LNB output to protect the IC against short circuits. The internal MOSFET will turn off when the LX current is higher than 3A cycle-by-cycle. The LNB output will turn off when the output current higher than the 550mA and 45ms and turn-on after 1800ms automatically.

Input Capacitor Selection

The input capacitor reduces voltage spikes from the input supply and minimizes noise injection to the converter. A 30μ F capacitance is sufficient for most applications. Nevertheless, a higher or lower value may be used depending on the noise level from the input supply and the input current to the converter. Note that the voltage rating of the input capacitor must be greater than the maximum input voltage.

Inductor Selection

The inductance depends on the maximum input current. As a general rule, the inductor ripple current range is 20% to 40% of the maximum input current. If 40% is selected as an example, the inductor ripple current can be calculated according to the following equations :

 $I_{IN(MAX)} = \frac{V_{OUT} \times I_{OUT(MAX)}}{\eta \times V_{IN}}$ $I_{RIPPLE} = 0.4 \times I_{IN(MAX)}$

where η is the efficiency of the converter, $I_{IN(MAX)}$ is the maximum input current, and IRIPPLE is the inductor ripple current. The input peak current can then be obtained by adding the maximum input current

with half of the inductor ripple current as shown in the following equation :

 $I_{PEAK} = 1.2 \text{ x } I_{IN(MAX)}$

note that the saturated current of the inductor must be greater than I_{PEAK} . The inductance can eventually be determined according to the following equation :

 $L = \frac{\eta \times (V_{IN})^2 \times (V_{OUT} - V_{IN})}{0.4 \times (V_{OUT})^2 \times I_{OUT(MAX)} \times f_{OSC}}$

where f_{OSC} is the switching frequency. For better system performance, a shielded inductor is preferred to avoid EMI problems.

Boost Output Capacitor Selection

The RT5047 boost regulator is internally compensated and relies on the inductor and output capacitor value for overall loop stability. The output capacitor is in the 30μ F to 50μ F range with a low ESR, as strongly recommended. The voltage rating on this capacitor should be in the 25V to 35V range since it is connected to the boost V_{OUT} rail.

The output ripple voltage is an important index for estimating chip performance. This portion consists of two parts. One is the product of the inductor current with the ESR of the output capacitor, while the other part is formed by the charging and discharging process of the output capacitor. As shown in Figure 1, ΔV_{OUT1} can be evaluated based on the ideal energy equalization. According to the definition of Q, the Q value can be calculated as the following equation :

$$Q = \frac{1}{2} \times \left[\left(I_{IN} + \frac{1}{2} \Delta I_L - I_{OUT} \right) + \left(I_{IN} - \frac{1}{2} \Delta I_L - I_{OUT} \right) \right]$$
$$\times \frac{V_{IN}}{V_{OUT}} \times \frac{1}{f_{OSC}} = C_{OUT} \times \Delta V_{OUT1}$$

where f_{OSC} is the switching frequency and ΔI_L is the inductor ripple current. Bring C_{OUT} to the left side to estimate the value of ΔV_{OUT1} according to the following equation :

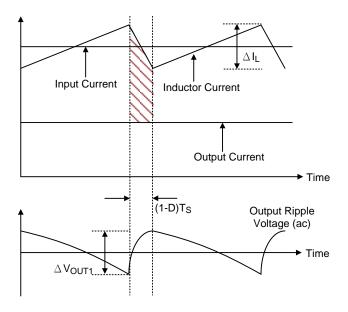
$$\Delta V_{OUT1} = \frac{D \times I_{OUT}}{\eta \times C_{OUT} \times f_{OSC}}$$

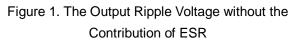
RT5047

where D is the duty cycle and η is the boost converter efficiency. Finally, take ESR into consideration, the overall output ripple voltage can be determined by the following equation :

 $\Delta V_{OUT} = I_{IN} \times ESR + \frac{D \times I_{OUT}}{\eta \times C_{OUT} \times f_{OSC}}$

The output capacitor, C_{OUT} , should be selected accordingly.





Schottky Diode Selection

Schottky diodes are chosen for their low forward-voltage drop and fast switching speed. However, when making a selection, important parameters such as power dissipation, reverse voltage rating, and pulsating peak current should all be taken into consideration. A suitable Schottky diode's reverse voltage rating must be greater than the maximum output voltage and its average current rating must exceed the average output current. The chosen diode should also have a sufficiently low leakage current level, since it increases with temperature.

Under-Voltage Lockout (UVLO)

The UVLO circuit compares the input voltage at VIN with the UVLO threshold (7.7V rising typically) to ensure that the input voltage is high enough for reliable

operation. The 350mV (typ.) hysteresis prevents supply transients from causing a shutdown. Once the input voltage exceeds the UVLO rising threshold, start-up begins. When the input voltage falls below the UVLO falling threshold, all IC internal functions will be turned off by the controller.

Over-Current Protection

The RT5047 features an over-current protection function to prevent chip damage from high peak currents. Both the boost converter and the linear regulator have independent current limit. In the boost converter, this is achieved through cycle-by-cycle internal current limit. During the ON-period, the chip senses the inductor current that is flowing into the LX pin. The internal NMOS will be turned off if the peak inductor current reaches the current-limit value of 3A (typ.).When the linear regulator exceeds 550mA (typ.) more than 45ms, the LNB output will be disabled. During this period of time, if the current limit condition disappears, the OCP will be cleared and the part restarts. If the part is still in current limit after this time period, the linear regulator and boost converter will automatically disable to prevent the part from overheating.

Short Circuit Protection

If the LNB output is shorted to ground, and more than 45ms, the RT5047 will be disabled 1.8s then enable automatically.

Over-Temperature Protection

When the junction temperature reaches the critical temperature (typically 140 °C), the boost converter and the linear regulator are immediately disabled. When the junction temperature cools down to a lower temperature threshold specified, the RT5047 will be allowed to restart by normal start operation.

LNB Output Voltage

The RT5047 has voltage control function on the LNB output. This function provides 4 levels for the common standards and compensation if the cable line has voltage drop. These voltage levels are defined in table 1. The rise time and fall time of the VLNB is 3mS (typ.).





Table 1						
SEL Pin Status	COMP Pin Status	LNB Output Voltage				
0	0	13.3V				
0	1	14.3V				
1	0	18.3V				
1	1	19.3V				

Tone Generation

The RT5047 provides the tone generation function, please refer to the Figure 2. Set the TONE pin with 22kHz logic signal, the LNB linear regulator output will carry a 22kHz, 700mV peak to peak signal for DiSEqC 1.x communication. It can meet base-band timings of $500\mu s$ (±100 μs) for a one-third bit PWK coded signal period on a nominal 22kHz (±20 %).

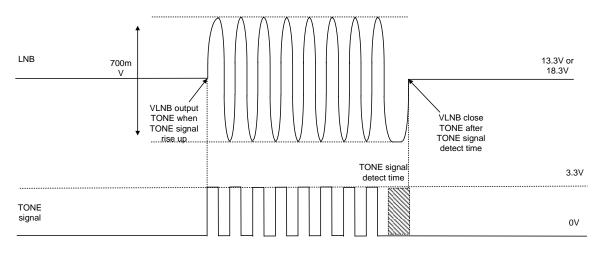


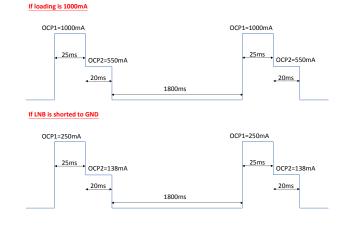
Figure 2. Tone Generation Options

Pull-Down Rate Control

The output linear stage provides approximately 40mA of pull-down capability. This ensures that the output volts are ramped from 18.3V to 13.3V in a reasonable amount of time.

Over-Current Disable Time

If the LNB output current exceeds 550mA, typical, for more than 45ms, then the LNB output will be disabled and device enters a TON = 45ms/TOFF = 1800msroutine. It will be returned to normal operation after a successful soft-start process.





Inrush Current

At start-up or during a LNB reconfiguration event, a transient surge current above the normal DC operating level can be provided by the IC. This current increase can be as high as 550mA, typical, for as long as required, up to a maximum of 45ms.

DC Current

The RT5047 can handle up to 500mA during continuous operation.

Thermal Considerations

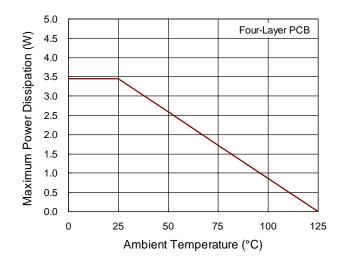
For continuous operation, do not exceed absolute maximum junction temperature. The maximum power dissipation depends on the thermal resistance of the IC package, PCB layout, rate of surrounding airflow, and difference between junction and ambient temperature. The maximum power dissipation can be calculated by the following formula :

$P_{D(MAX)} = (T_{J(MAX)} - T_{A}) / \theta_{JA}$

where $T_{J(MAX)}$ is the maximum junction temperature, T_A is the ambient temperature, and θ_{JA} is the junction to ambient thermal resistance.For recommended operating condition specifications, the maximum junction temperature is 125°C. The junction to ambient thermal resistance, θ_{JA} , is layout dependent. For SOP-8 (Exposed Pad) package, the thermal resistance, θJA, is 29°C/W on a standard JEDEC 51-7 four-layer thermal test board. The maximum power dissipation at $T_A = 25^{\circ}C$ can be calculated by the following formula :

 $P_{D(MAX)} = (125^{\circ}C - 25^{\circ}C) / (29^{\circ}C/W) = 3.44W$ for SOP-8 (Exposed Pad) package

The maximum power dissipation depends on the operating ambient temperature for fixed $T_{J(MAX)}$ and thermal resistance, θ_{JA} . The derating curve in Figure 3 allows the designer to see the effect of rising ambient temperature on the maximum power dissipation.



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Figure 3. Derating Curve of Maximum Power Dissipation

Layout Consideration

For high frequency switching power supplies, the PCB layout is important to get good regulation, high efficiency and stability. The following descriptions are the guidelines for better PCB layout.

- ► For good regulation, place the power components as close as possible. The traces should be wide and short enough especially for the high-current loop.
- ▶ Minimize the size of the LX node and keep it wide and shorter.
- ► The exposed pad of the chip should be connected to a strong ground plane for maximum thermal consideration.

 D_3 and D_4 should be placed The exposed pad of the chip The CIN, CBST and CLNB should be connected to as closed as possible to should be placed as closed analog ground plane for as possible to the RT5047 V_{OUT} for surge protection. thermal consideration. for good filter. V_{OUT} LN₿ TOME D₂ COMP BOOST The TONE, SEL and EN pin CBST CBST GND should be connected to MCU CBS or GND. Do not floating these 0 LX SEL pins. VIN 0 ΕN 'IN \square CIN₁ CIN₂

The inductor should be placed as close as possible to the LX pin to minimize the noise coupling into other circuits.

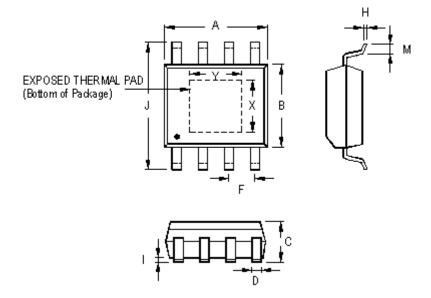
LX node copper area should be minimized for reducing EMI

Place the power components as close as possible. The traces should be wide and short especially for the high-current loop.

Figure 4. PCB Layout Guide



Outline Dimension



Symbol		Dimensions I	n Millimeters	Dimensions In Inches		
		Min	Max	Min	Max	
А		4.801	5.004	0.189	0.197	
В		3.810	4.000	0.150	0.157	
С		1.346	1.753	0.053	0.069	
D		0.330	0.510	0.013	0.020	
F		1.194	1.346	0.047	0.053	
н		0.170	0.254	0.007	0.010	
I		0.000	0.152	0.000	0.006	
J		5.791	6.200	0.228	0.244	
М		0.406	1.270	0.016	0.050	
Option 1	Х	2.000	2.300	0.079	0.091	
Option 1	Y	2.000	2.300	0.079	0.091	
Option 2	Х	2.100	2.500	0.083	0.098	
Option 2	Y	3.000	3.500	0.118	0.138	

8-Lead SOP (Exposed Pad) Plastic Package

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